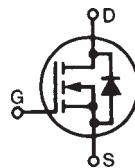


**HiPerFET™
Power MOSFET
Q2-Class**

IXFR38N80Q2



V_{DSS} = **800V**
 I_{D25} = **28A**
 $R_{DS(on)}$ ≤ **240mΩ**
 t_{rr} ≤ **250ns**

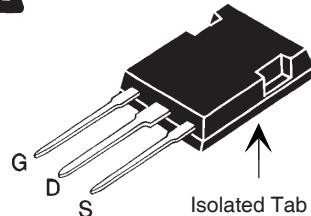
(Electrically Isolated Back Surface)

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	800	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1\text{M}\Omega$	800	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	28	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	150	A
I_A	$T_C = 25^\circ\text{C}$	38	A
E_{AS}	$T_C = 25^\circ\text{C}$	4	J
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	20	V/ns
P_D	$T_C = 25^\circ\text{C}$	500	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum lead temperature for soldering	300	°C
T_{SOLD}	Plastic body for 10s	260	°C
V_{ISOL}	50/60 Hz, RMS, 1 minute	2500	V~
F_c	Mounting force	20..120/4.5..27	N/lb.
Weight		5	g

ISOPLUS247 (IXFR)



E153432



G = Gate D = Drain
S = Source

Features

- Double metal process for low gate resistance
- Silicon chip on DCB substrate
 - High power dissipation
 - Isolated mounting surface
 - 2500V electrical isolation
- Epoxy meet UL 94 V-0, flammability classification
- Avalanche energy and current rated
- Fast intrinsic Rectifier

Advantages

- Easy assembly
- Space savings
- High power density

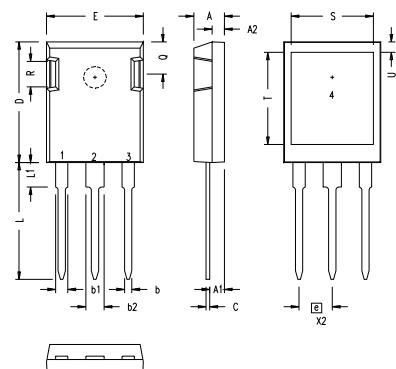
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0\text{V}$, $I_D = 3\text{mA}$	800		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8\text{mA}$	3.0		V
I_{GSS}	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0\text{V}$			25 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 19\text{A}$, Note 1			240 mΩ

Symbol	Test Conditions (T _J = 25°C unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 10V, I _D = 19A, Note 1	25	37	S
C_{iss} C_{oss} C_{rss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	9500	pF	
		888	pF	
		185	pF	
t_{d(on)} t_r t_{d(off)} t_f	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 19A R _G = 1Ω (External)	20	ns	
		16	ns	
		60	ns	
		12	ns	
Q_{g(on)} Q_{gs} Q_{gd}	V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 19A	190	nC	
		44	nC	
		88	nC	
R_{thJC}			0.25 °C/W	
R_{thCS}		0.15	°C/W	

Source-Drain Diode		Characteristic Values		
	T _J = 25°C unless otherwise specified)	Min.	Typ.	Max.
I_s	V _{GS} = 0V			38 A
I_{SM}	Repetitive, pulse width limited by T _{JM}			150 A
V_{SD}	I _F = I _S , V _{GS} = 0V, Note 1			1.5 V
t_{rr} Q_{RM} I_{RM}	I _F = 25A, -di/dt = 100A/μs V _R = 100V, V _{GS} = 0V	1	250 ns	μC
		10		A

Note 1: Pulse test, t ≤ 300μs; duty cycle, d ≤ 2%.

ISOPLUS247 (IXFR) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

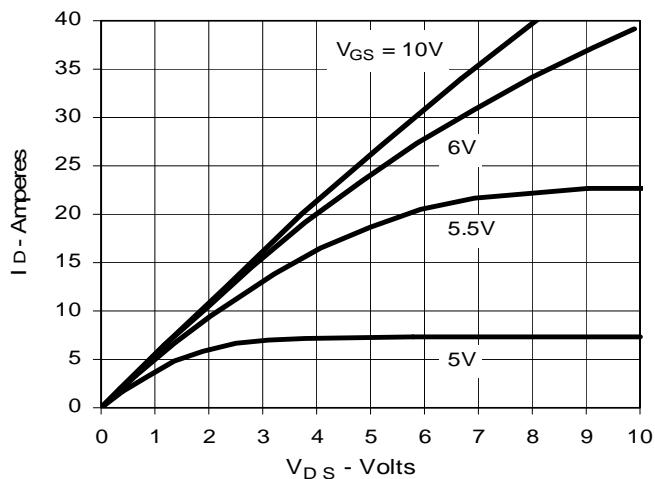
1 – GATE
2 – DRAIN (COLLECTOR)
3 – SOURCE (EMITTER)
4 – NO CONNECTION

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.

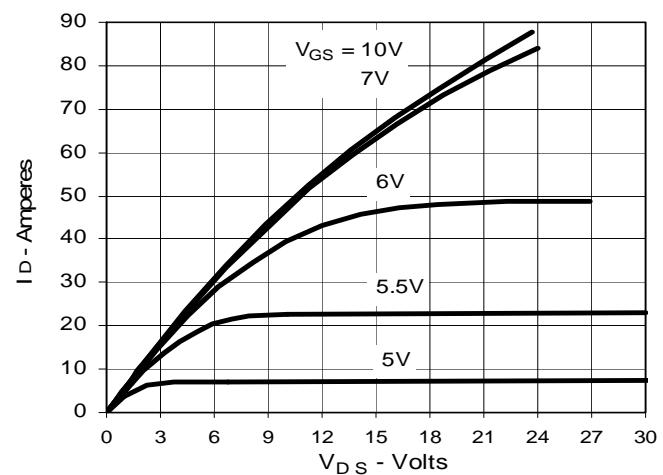
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

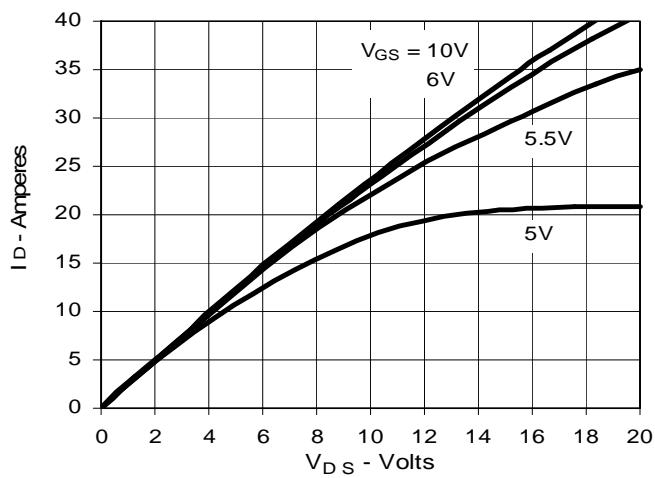
**Fig. 1. Output Characteristics
@ 25°C**



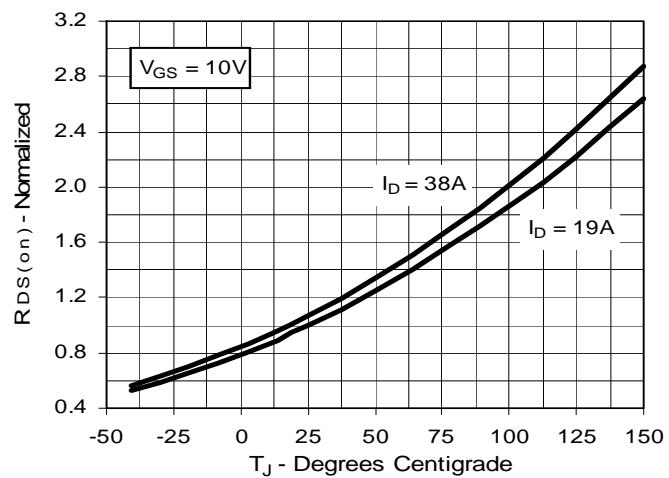
**Fig. 2. Extended Output Characteristics
@ 25°C**



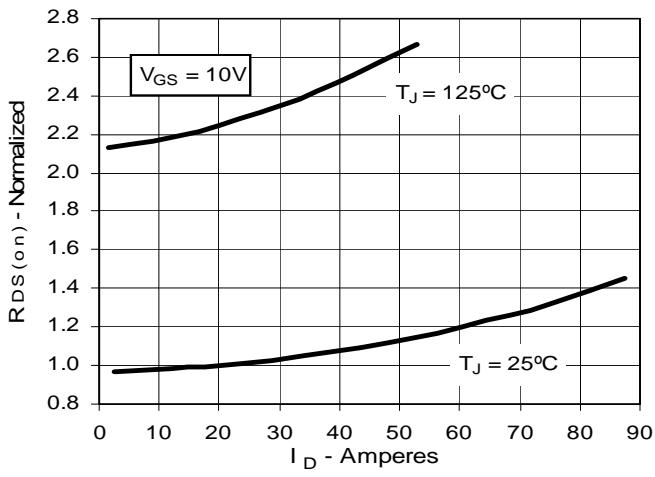
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value
vs. I_D**



**Fig. 6. Drain Current vs. Case
Temperature**

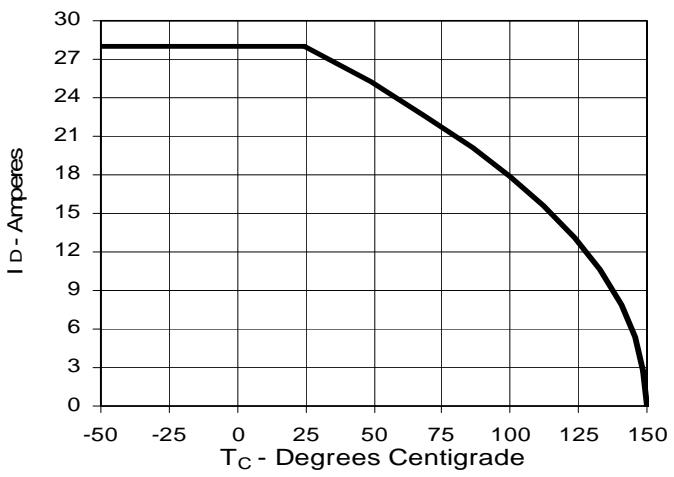
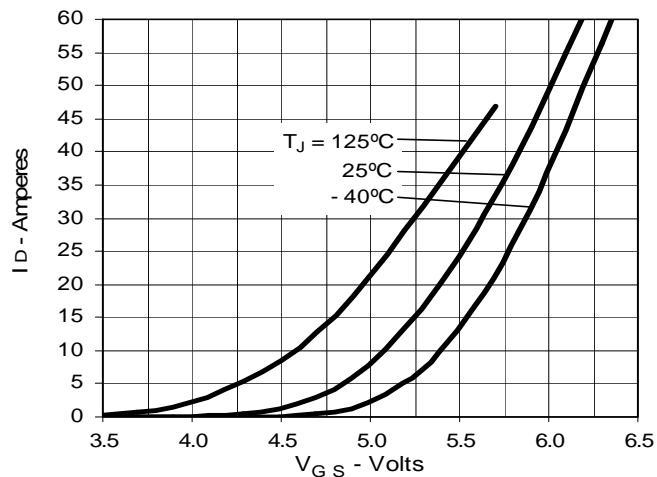
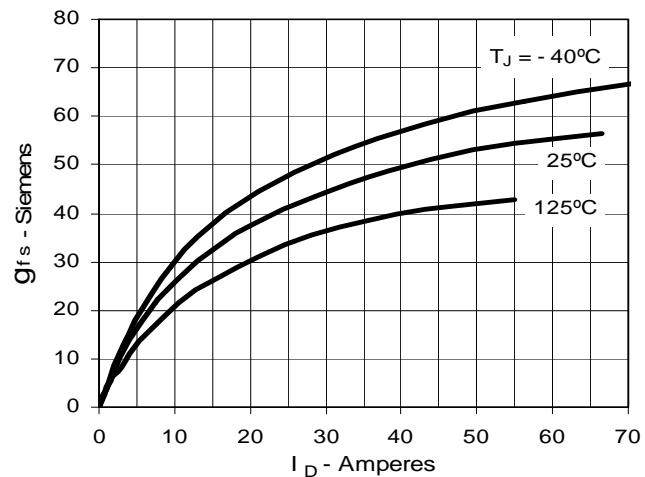
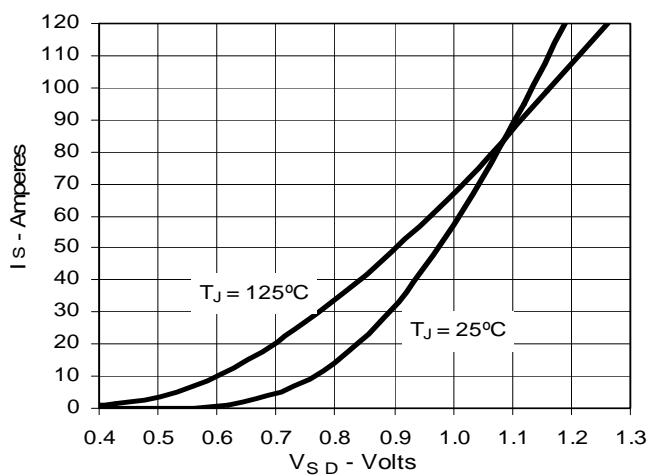
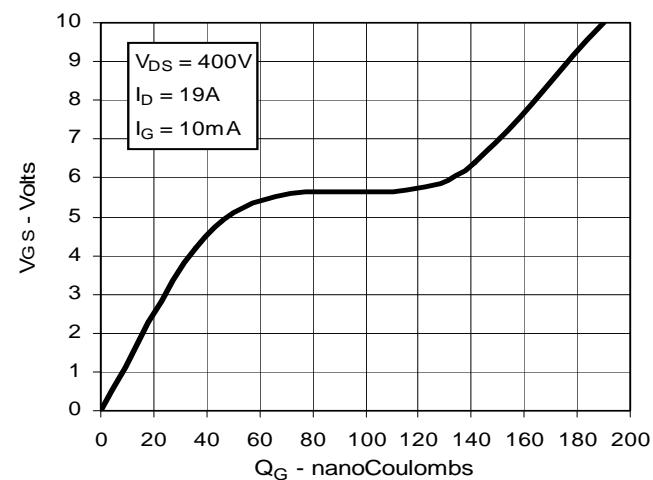
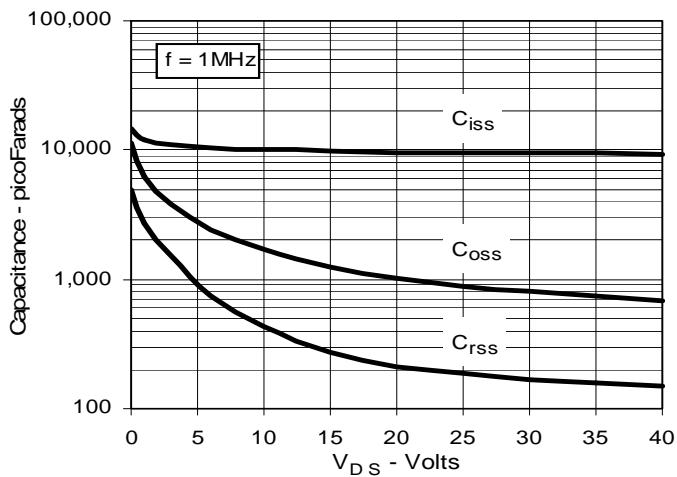
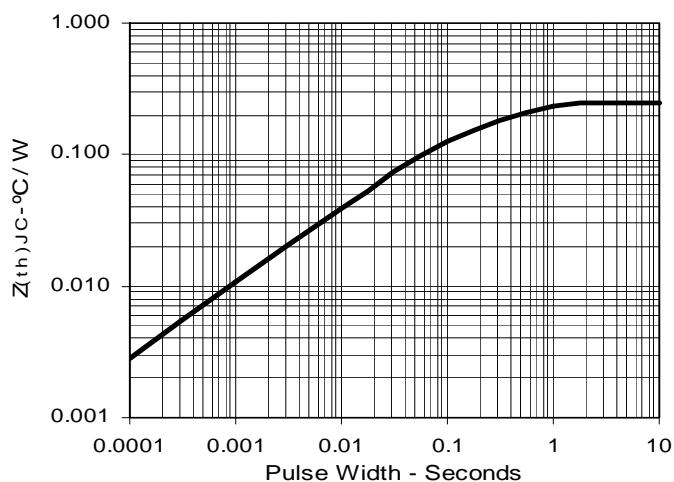


Fig. 7. Input Admittance**Fig. 8. Transconductance****Fig. 9. Source Current vs. Source-To-Drain Voltage****Fig. 10. Gate Charge****Fig. 11. Capacitance****Fig. 12. Maximum Transient Thermal Impedance**



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